

N-channel 650 V, 0.073 Ω typ., 30 A MDmesh™ V Power MOSFETs in D²PAK, TO-220 and TO-247 packages

Datasheet - production data

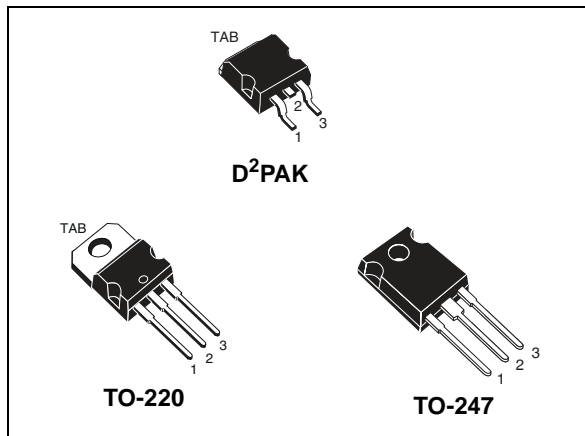
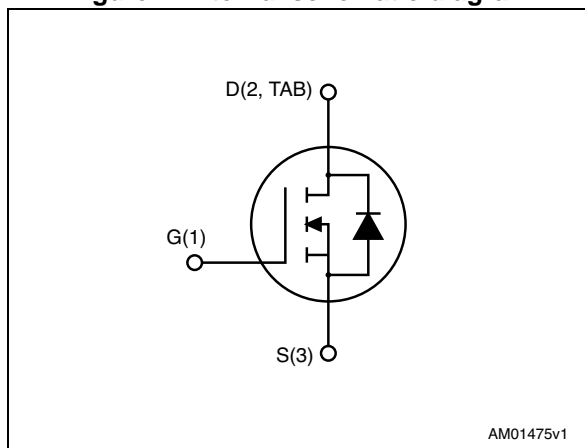


Figure 1. Internal schematic diagram



Features

| Order codes | $V_{DS} @ T_{Jmax}$ | $R_{DS(on) max}$ | I_D |
|-------------|---------------------|------------------|-------|
| STB38N65M5 | 710 V | 0.095 Ω | 30 A |
| STP38N65M5 | | | |
| STW38N65M5 | | | |

- Higher V_{DSS} rating and high dv/dt capability
- Excellent switching performance
- 100% avalanche tested

Applications

- Switching applications

Description

These devices are N-channel MDmesh™ V Power MOSFETs based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

Table 1. Device summary

| Order codes | Marking | Package | Packaging |
|-------------|---------|--------------------|---------------|
| STB38N65M5 | 38N65M5 | D ² PAK | Tape and reel |
| STP38N65M5 | | TO-220 | Tube |
| STW38N65M5 | | TO-247 | |

Contents

- 1 Electrical ratings 3**
- 2 Electrical characteristics 4**
 - 2.1 Electrical characteristics (curves) 6
- 3 Test circuits 9**
- 4 Package mechanical data 10**
 - 4.1 D2PAK, STB38N65M511
 - 4.2 TO-220, STP38N65M5 14
 - 4.3 TO-247, STW38N65M5 16
- 5 Packaging mechanical data 18**
- 6 Revision history 20**

1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|---|-------------|------------------|
| V_{GS} | Gate-source voltage | ± 25 | V |
| I_D | Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$ | 30 | A |
| I_D | Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$ | 19 | A |
| $I_{DM}^{(1)}$ | Drain current (pulsed) | 120 | A |
| P_{TOT} | Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ | 190 | W |
| $dv/dt^{(2)}$ | Peak diode recovery voltage slope | 15 | V/ns |
| $dv/dt^{(3)}$ | MOSFET dv/dt ruggedness | 50 | V/ns |
| T_{stg} | Storage temperature | - 55 to 150 | $^\circ\text{C}$ |
| T_j | Max. operating junction temperature | 150 | $^\circ\text{C}$ |

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 30\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{Peak} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$
3. $V_{DS} \leq 520\text{ V}$

Table 3. Thermal data

| Symbol | Parameter | Value | | | Unit |
|----------------|--|--------------------|--------|--------|---------------------------|
| | | D ² PAK | TO-220 | TO-247 | |
| $R_{thj-case}$ | Thermal resistance junction-case max | 0.66 | | | $^\circ\text{C}/\text{W}$ |
| $R_{thj-pcb}$ | Thermal resistance junction-pcb max ⁽¹⁾ | 30 | | | $^\circ\text{C}/\text{W}$ |
| $R_{thj-amb}$ | Thermal resistance junction-ambient max | | 62.5 | 50 | $^\circ\text{C}/\text{W}$ |

1. When mounted on 1inch² FR-4 board, 2 oz Cu.

Table 4. Avalanche characteristics

| Symbol | Parameter | Value | Unit |
|----------|--|-------|------|
| I_{AR} | Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax}) | 8 | A |
| E_{AS} | Single pulse avalanche energy (starting $t_j = 25\text{ }^\circ\text{C}$, $I_d = I_{AR}$; $V_{dd} = 50\text{ V}$) | 660 | mJ |

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|-------|-----------|---------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $I_D = 1\text{ mA}$, $V_{GS} = 0$ | 650 | | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = 650\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 650\text{ V}$, $T_C = 125\text{ °C}$ | | | 100 | μA |
| I_{GSS} | Gate-body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 25\text{ V}$ | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 3 | 4 | 5 | V |
| $R_{DS(on)}$ | Static drain-source on-resistance | $V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$ | | 0.073 | 0.095 | Ω |

Table 6. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-------------------|---------------------------------------|---|------|------|------|----------|
| C_{iss} | Input capacitance | $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$ | - | 3000 | - | pF |
| C_{oss} | Output capacitance | | - | 74 | - | pF |
| C_{riss} | Reverse transfer capacitance | | - | 5.8 | - | pF |
| $C_{o(tr)}^{(1)}$ | Equivalent capacitance time related | $V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0$ | - | 244 | - | pF |
| $C_{o(er)}^{(2)}$ | Equivalent capacitance energy related | | - | 70 | - | pF |
| R_G | Intrinsic gate resistance | $f = 1\text{ MHz}$ open drain | - | 2.4 | - | Ω |
| Q_g | Total gate charge | $V_{DD} = 520\text{ V}$, $I_D = 15\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 18) | - | 71 | - | nC |
| Q_{gs} | Gate-source charge | | - | 18 | - | nC |
| Q_{gd} | Gate-drain charge | | - | 30 | - | nC |

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------|--------------------|--|------|------|------|------|
| $t_d(v)$ | Voltage delay time | $V_{DD} = 400\text{ V}$, $I_D = 20\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 19 and Figure 22) | - | 66 | - | ns |
| $t_r(v)$ | Voltage rise time | | - | 9 | - | ns |
| $t_f(i)$ | Current fall time | | - | 9 | - | ns |
| $t_{c(off)}$ | Crossing time | | - | 13 | - | ns |

Table 8. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|-------------------------------|--|------|------|------|---------------|
| I_{SD} | Source-drain current | | - | | 30 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | - | | 120 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 30\text{ A}$, $V_{GS} = 0$ | - | | 1.5 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 30\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 22) | - | 382 | | ns |
| Q_{rr} | Reverse recovery charge | | - | 6.6 | | μC |
| I_{RRM} | Reverse recovery current | | - | 35 | | A |
| t_{rr} | Reverse recovery time | $I_{SD} = 30\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 22) | - | 522 | | ns |
| Q_{rr} | Reverse recovery charge | | - | 10.3 | | μC |
| I_{RRM} | Reverse recovery current | | - | 40 | | A |

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D²PAK and TO-220

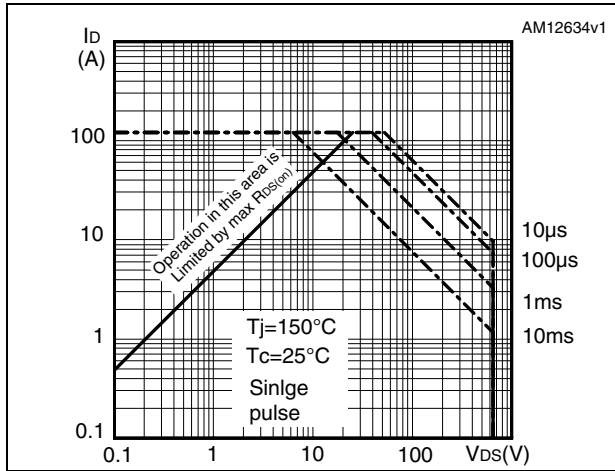


Figure 3. Thermal impedance for D²PAK and TO-220

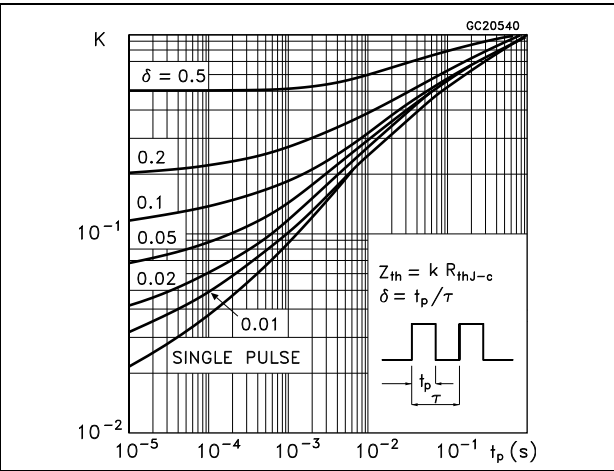


Figure 4. Safe operating area for TO-247

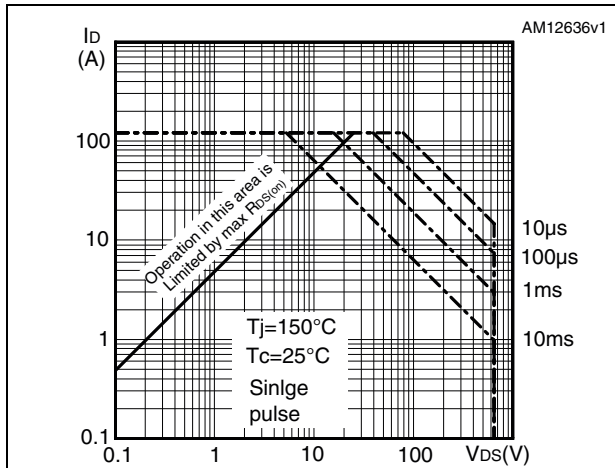


Figure 5. Thermal impedance for TO-247

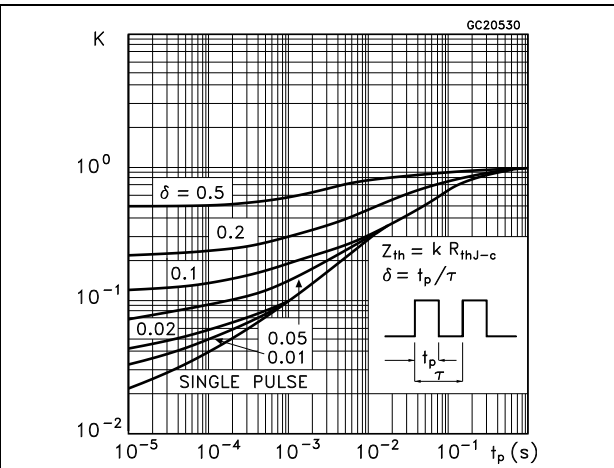


Figure 6. Output characteristics

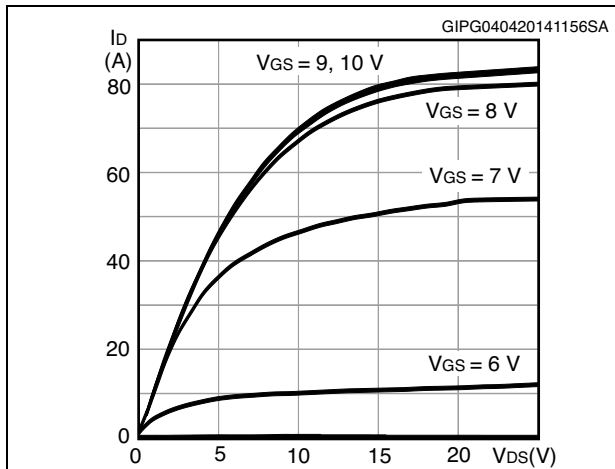


Figure 7. Transfer characteristics

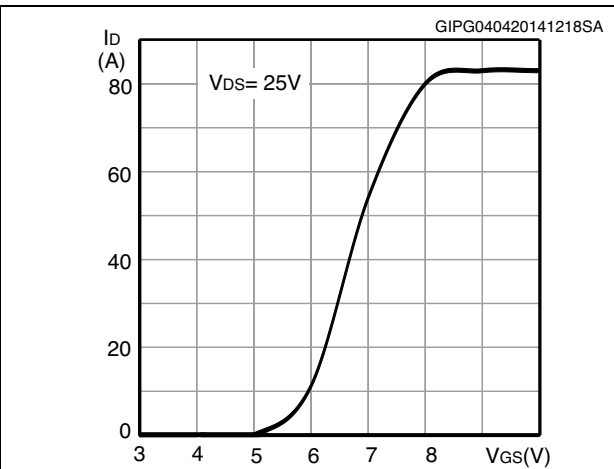


Figure 8. Gate charge vs gate-source voltage

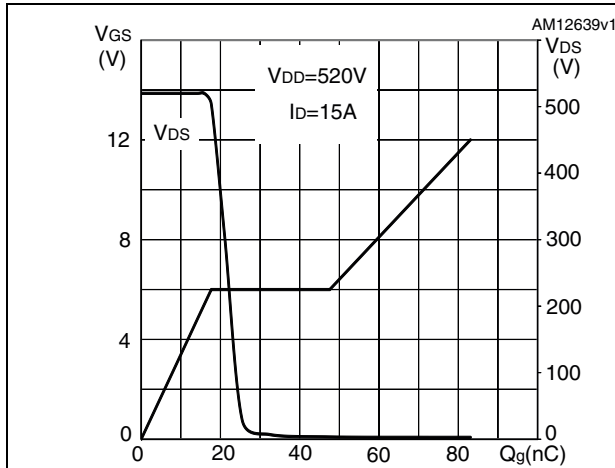


Figure 9. Static drain-source on-resistance

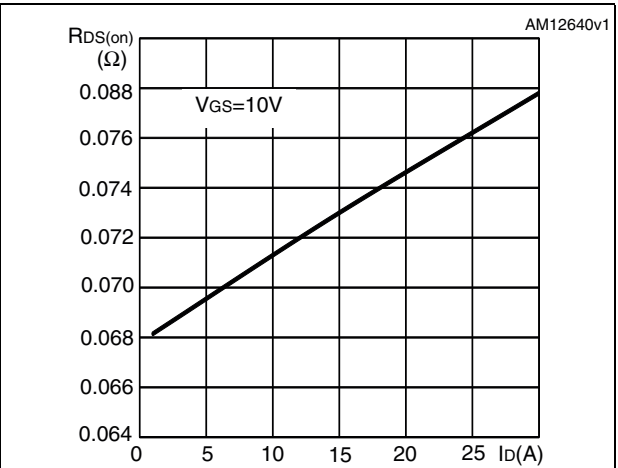


Figure 10. Capacitance variations

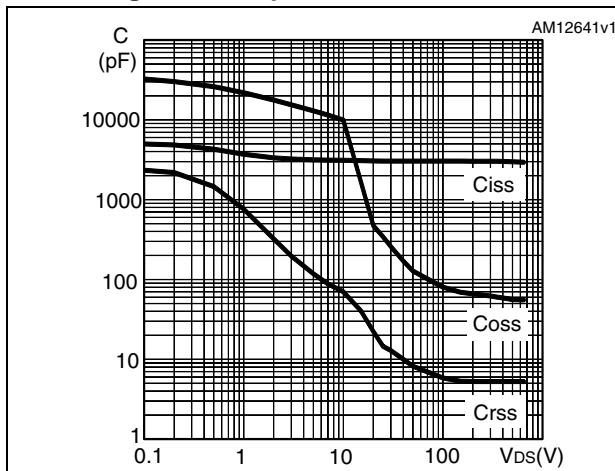


Figure 11. Output capacitance stored energy

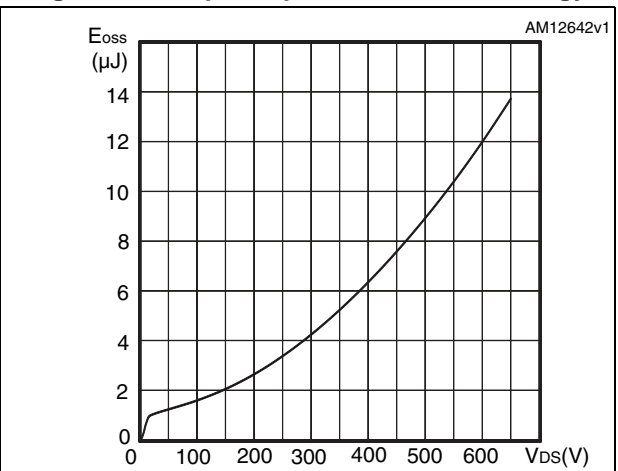


Figure 12. Normalized gate threshold voltage vs temperature

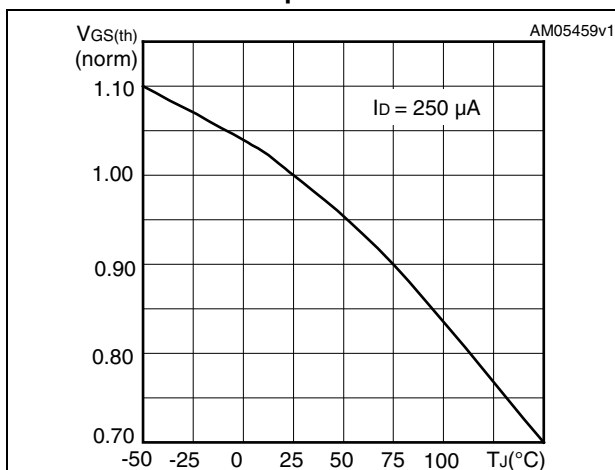


Figure 13. Normalized on-resistance vs temperature

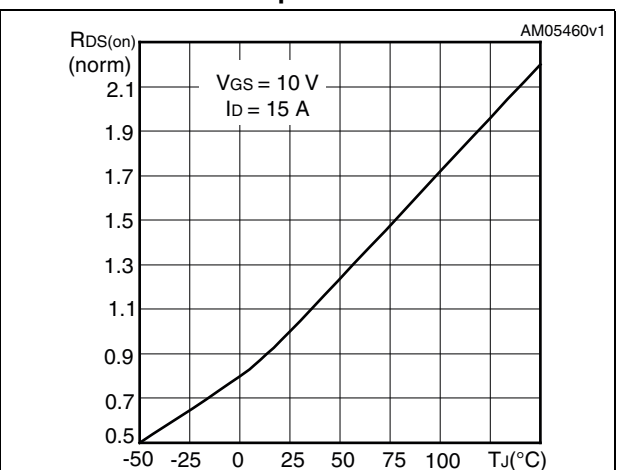


Figure 14. Source-drain diode forward characteristics

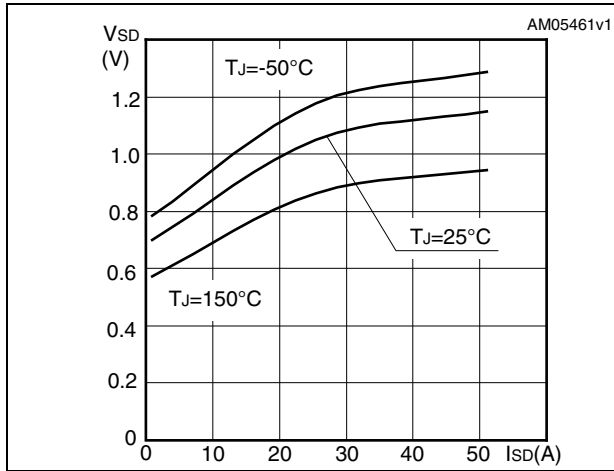


Figure 15. Normalized $V_{(BR)DSS}$ vs temperature

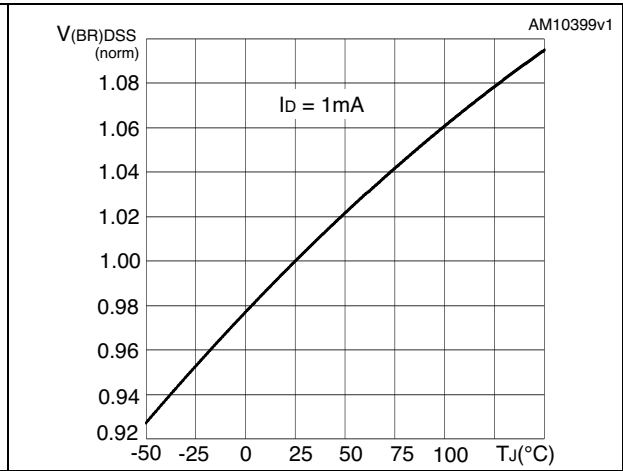
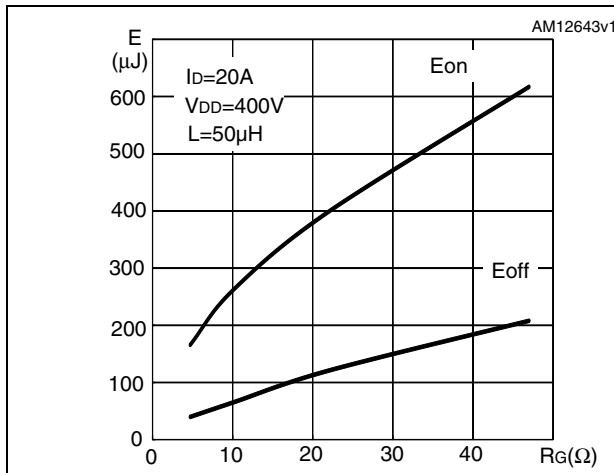


Figure 16. Switching losses vs gate resistance (1)



1. E_{on} including reverse recovery of a SiC diode.

3 Test circuits

Figure 17. Switching times test circuit for resistive load

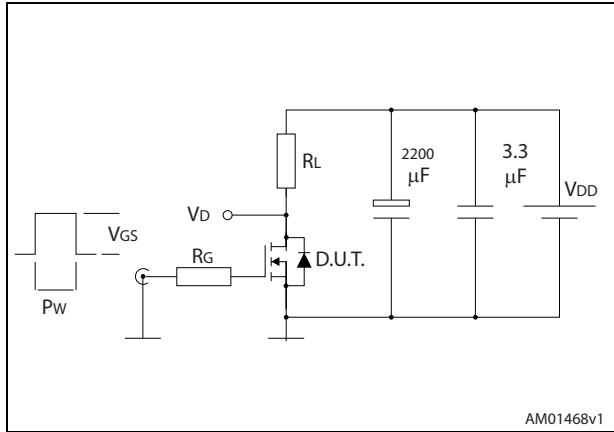


Figure 18. Gate charge test circuit

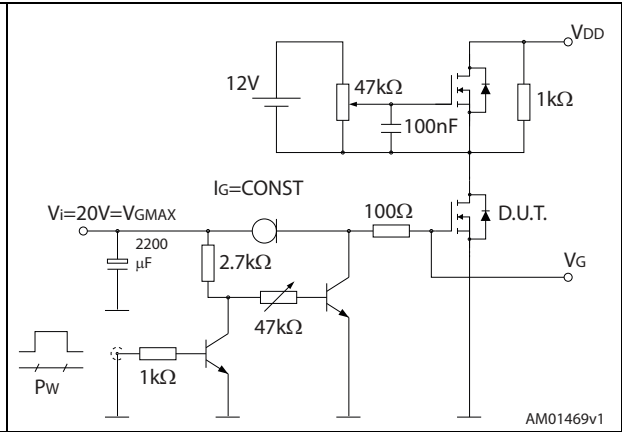


Figure 19. Test circuit for inductive load switching and diode recovery times

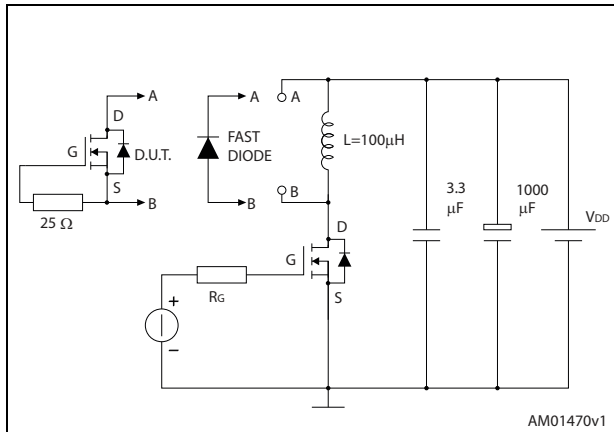


Figure 20. Unclamped inductive load test circuit

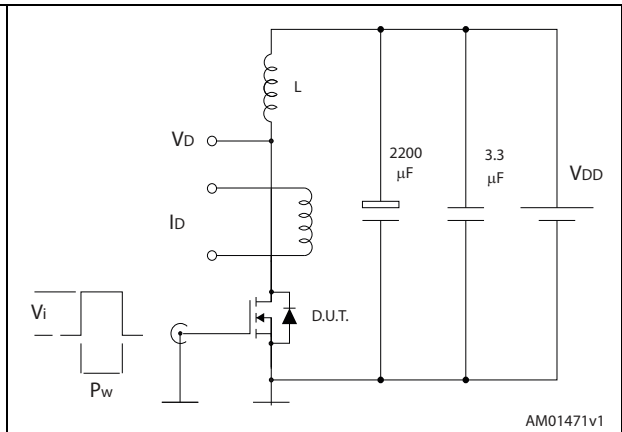


Figure 21. Unclamped inductive waveform

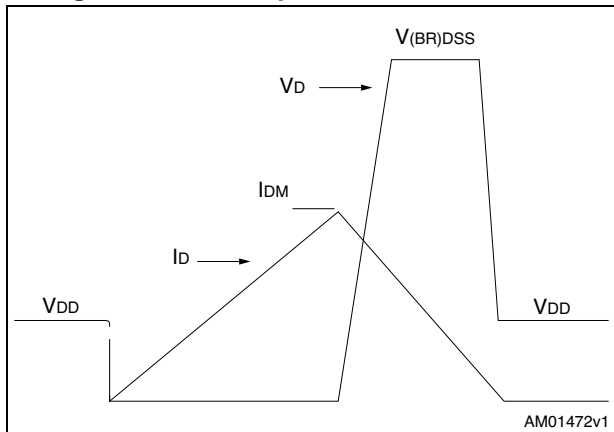
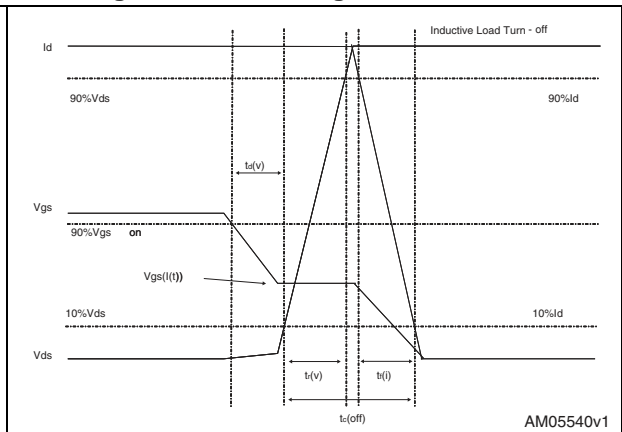


Figure 22. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

4.1 D²PAK, STB38N65M5

Figure 23. D²PAK (TO-263) drawing

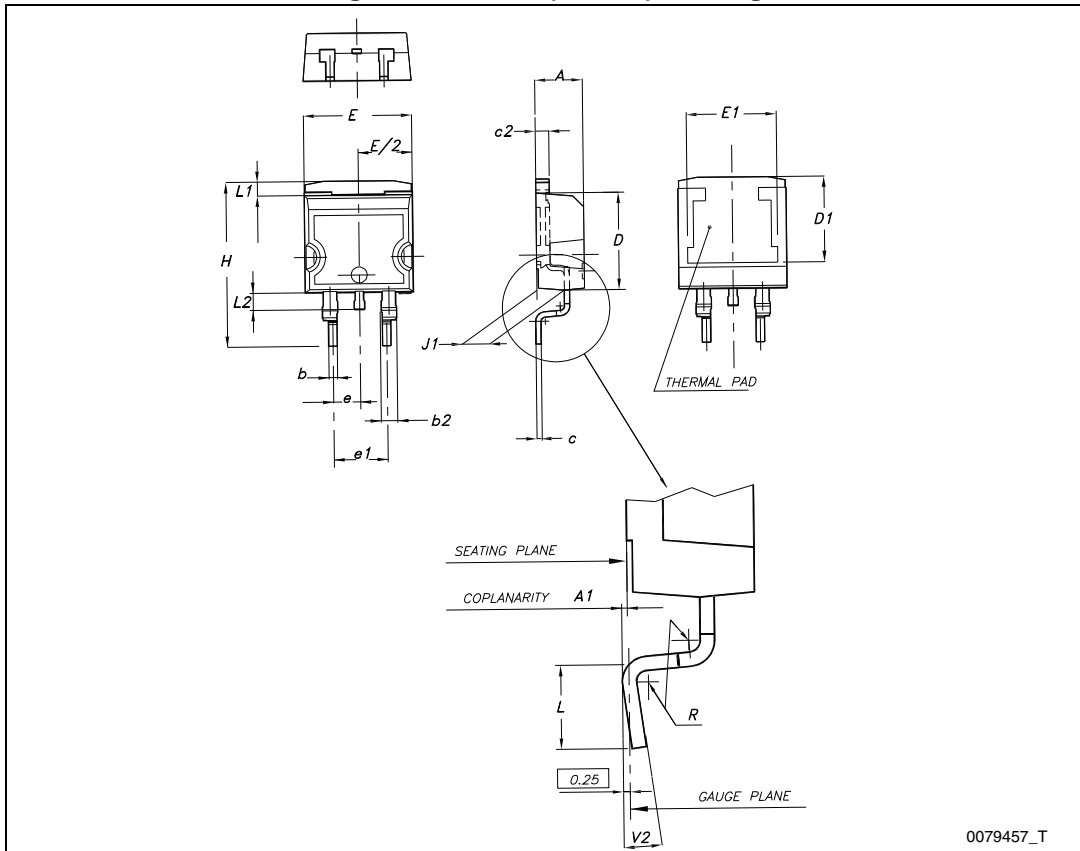
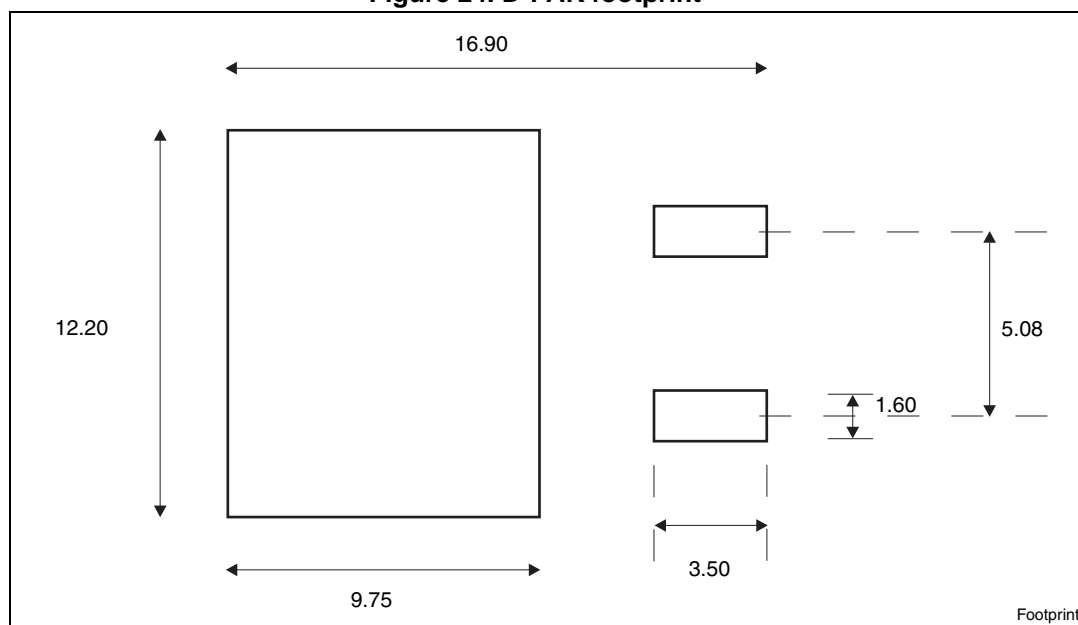


Table 9. D²PAK (TO-263) mechanical data

| Dim. | mm | | |
|------|------|------|-------|
| | Min. | Typ. | Max. |
| A | 4.40 | | 4.60 |
| A1 | 0.03 | | 0.23 |
| b | 0.70 | | 0.93 |
| b2 | 1.14 | | 1.70 |
| c | 0.45 | | 0.60 |
| c2 | 1.23 | | 1.36 |
| D | 8.95 | | 9.35 |
| D1 | 7.50 | | |
| E | 10 | | 10.40 |
| E1 | 8.50 | | |
| e | | 2.54 | |
| e1 | 4.88 | | 5.28 |
| H | 15 | | 15.85 |
| J1 | 2.49 | | 2.69 |
| L | 2.29 | | 2.79 |
| L1 | 1.27 | | 1.40 |
| L2 | 1.30 | | 1.75 |
| R | | 0.4 | |
| V2 | 0° | | 8° |

Figure 24. D²PAK footprint^(a)



a. All dimension are in millimeters

4.2 TO-220, STP38N65M5

Figure 25. TO-220 type A drawing

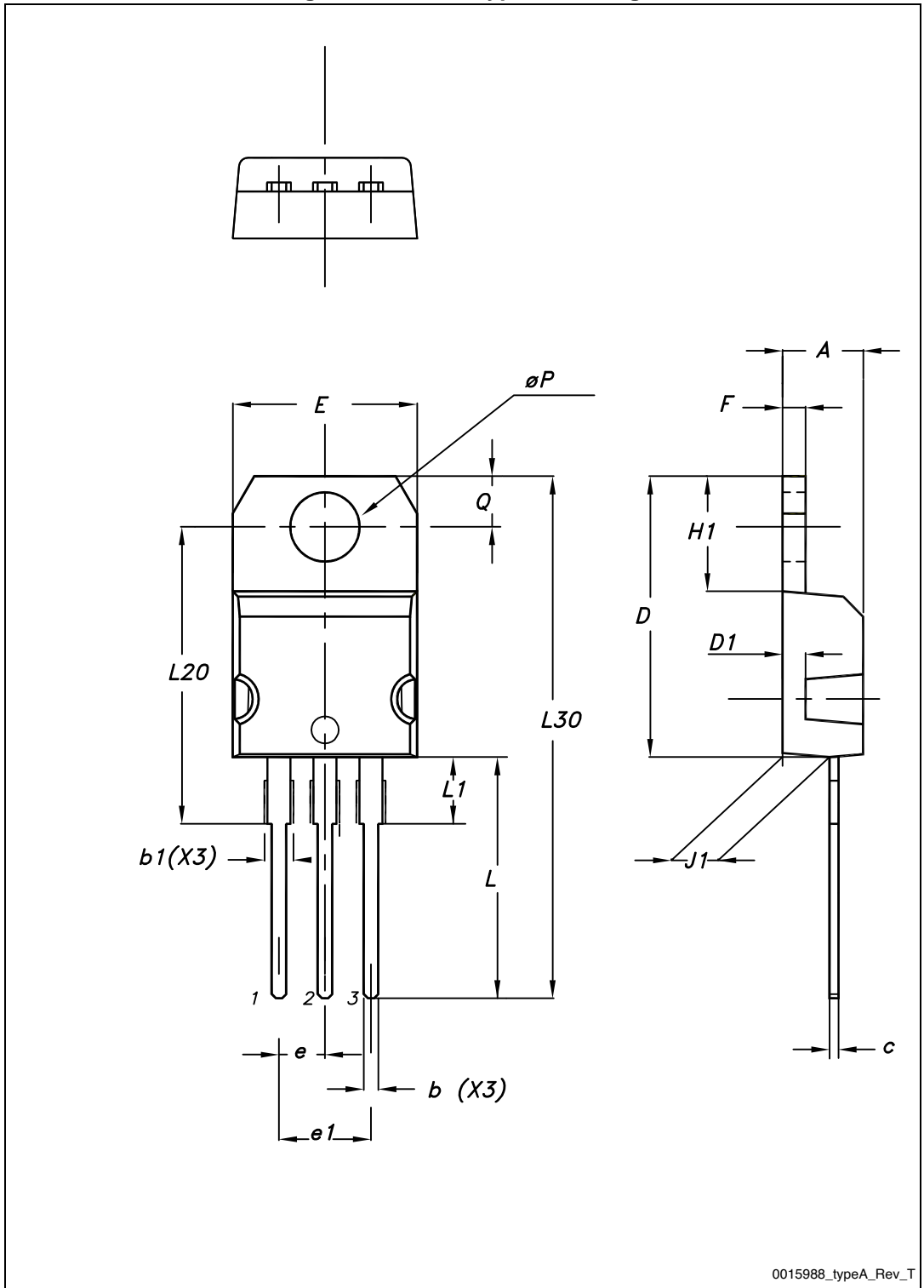


Table 10. TO-220 type A mechanical data

| Dim. | mm | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.40 | | 4.60 |
| b | 0.61 | | 0.88 |
| b1 | 1.14 | | 1.70 |
| c | 0.48 | | 0.70 |
| D | 15.25 | | 15.75 |
| D1 | | 1.27 | |
| E | 10 | | 10.40 |
| e | 2.40 | | 2.70 |
| e1 | 4.95 | | 5.15 |
| F | 1.23 | | 1.32 |
| H1 | 6.20 | | 6.60 |
| J1 | 2.40 | | 2.72 |
| L | 13 | | 14 |
| L1 | 3.50 | | 3.93 |
| L20 | | 16.40 | |
| L30 | | 28.90 | |
| ØP | 3.75 | | 3.85 |
| Q | 2.65 | | 2.95 |

4.3 TO-247, STW38N65M5

Figure 26. TO-247 drawing

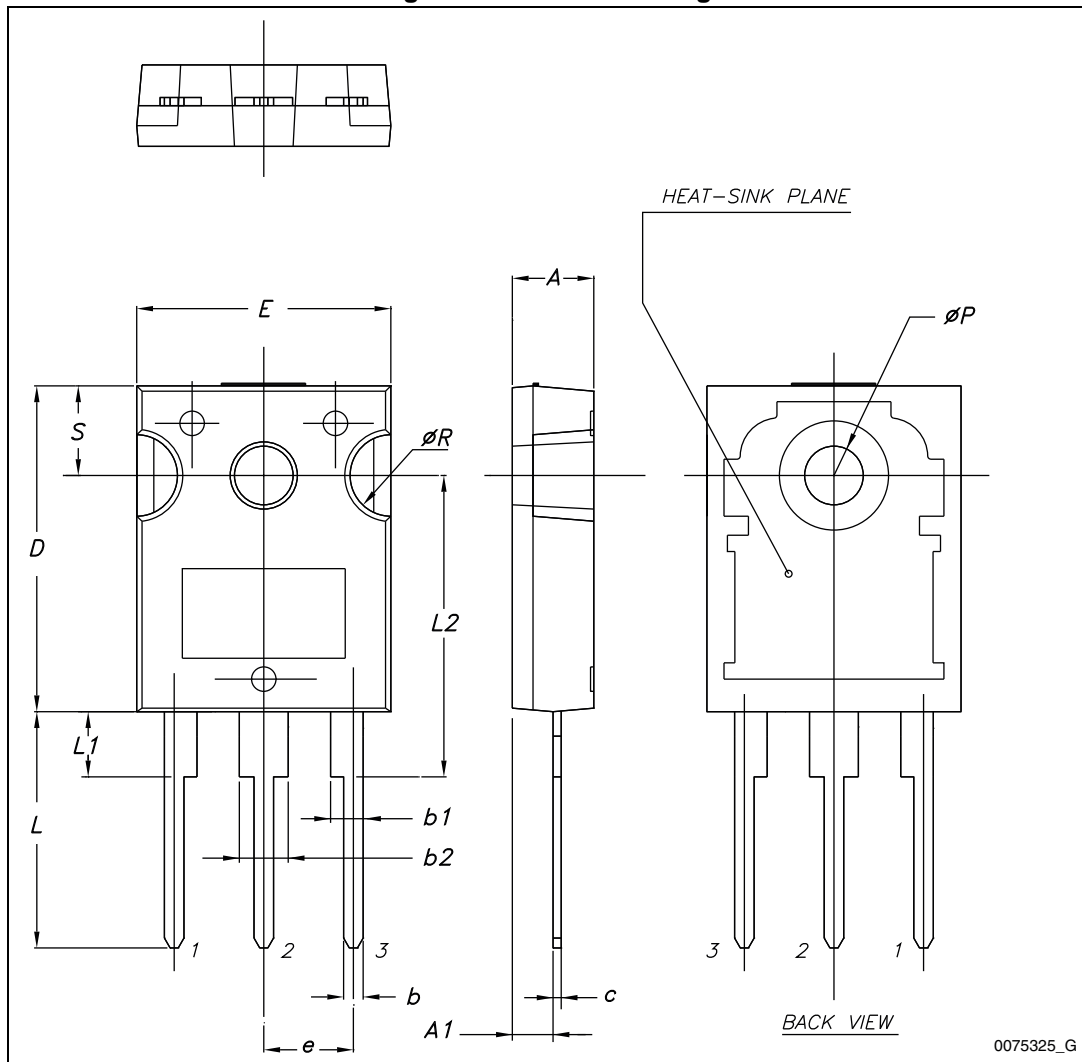


Table 11. TO-247 mechanical data

| Dim. | mm. | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.85 | | 5.15 |
| A1 | 2.20 | | 2.60 |
| b | 1.0 | | 1.40 |
| b1 | 2.0 | | 2.40 |
| b2 | 3.0 | | 3.40 |
| c | 0.40 | | 0.80 |
| D | 19.85 | | 20.15 |
| E | 15.45 | | 15.75 |
| e | 5.30 | 5.45 | 5.60 |
| L | 14.20 | | 14.80 |
| L1 | 3.70 | | 4.30 |
| L2 | | 18.50 | |
| ØP | 3.55 | | 3.65 |
| ØR | 4.50 | | 5.50 |
| S | 5.30 | 5.50 | 5.70 |

5 Packaging mechanical data

Figure 27. Tape

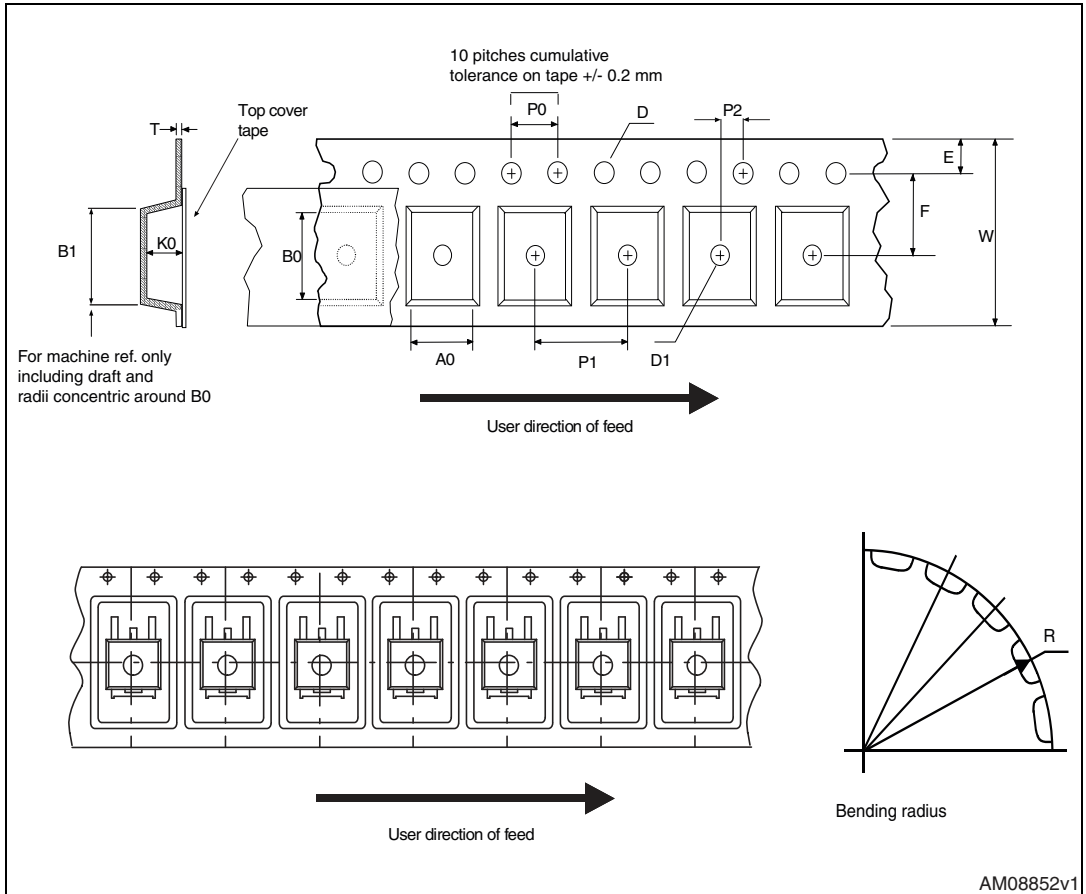


Figure 28. Reel

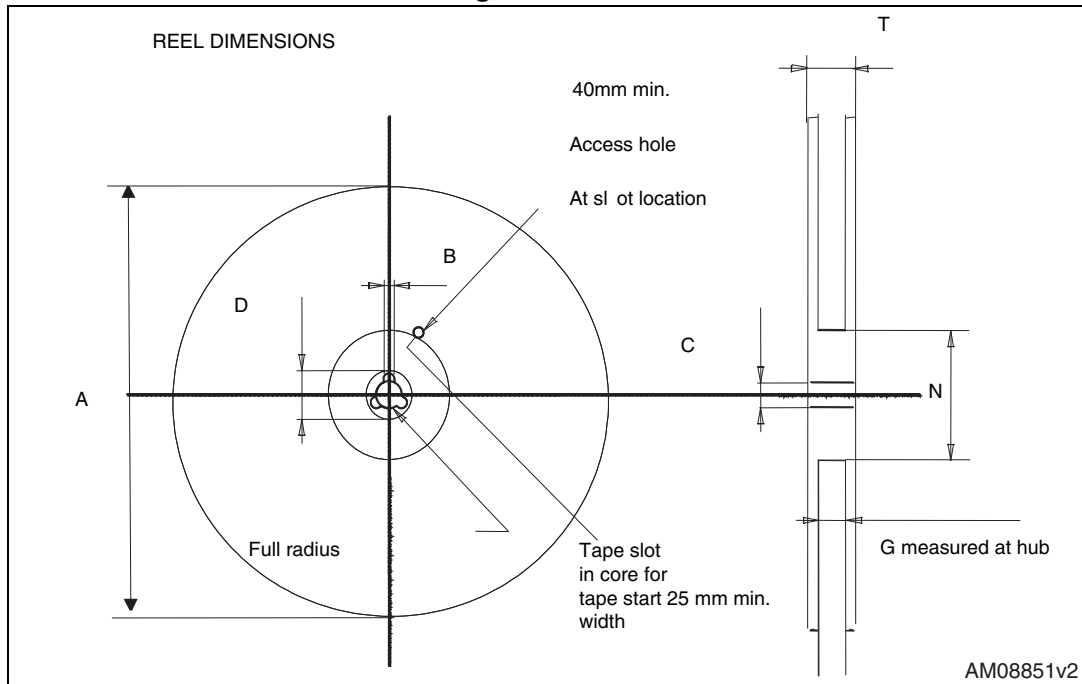


Table 12. D²PAK (TO-263) tape and reel mechanical data

| Tape | | | Reel | | |
|------|------|------|----------|------|------|
| Dim. | mm | | Dim. | mm | |
| | Min. | Max. | | Min. | Max. |
| A0 | 10.5 | 10.7 | A | | 330 |
| B0 | 15.7 | 15.9 | B | 1.5 | |
| D | 1.5 | 1.6 | C | 12.8 | 13.2 |
| D1 | 1.59 | 1.61 | D | 20.2 | |
| E | 1.65 | 1.85 | G | 24.4 | 26.4 |
| F | 11.4 | 11.6 | N | 100 | |
| K0 | 4.8 | 5.0 | T | | 30.4 |
| P0 | 3.9 | 4.1 | | | |
| P1 | 11.9 | 12.1 | Base qty | | 1000 |
| P2 | 1.9 | 2.1 | Bulk qty | | 1000 |
| R | 50 | | | | |
| T | 0.25 | 0.35 | | | |
| W | 23.7 | 24.3 | | | |

6 Revision history

Table 13. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 22-Feb-2012 | 1 | First release. |
| 21-Jun-2012 | 2 | Document status changed from preliminary data to production data. Added Section 2.1: Electrical characteristics (curves) . |
| 05-Mar-2013 | 3 | Added dv/dt value on Table 2: Absolute maximum ratings . |
| 09-Apr-2014 | 4 | <ul style="list-style-type: none">– The part number STF38N65M5 has been moved to a separate datasheet– Minor text changes |

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

ST PRODUCTS ARE NOT DESIGNED OR AUTHORIZED FOR USE IN: (A) SAFETY CRITICAL APPLICATIONS SUCH AS LIFE SUPPORTING, ACTIVE IMPLANTED DEVICES OR SYSTEMS WITH PRODUCT FUNCTIONAL SAFETY REQUIREMENTS; (B) AERONAUTIC APPLICATIONS; (C) AUTOMOTIVE APPLICATIONS OR ENVIRONMENTS, AND/OR (D) AEROSPACE APPLICATIONS OR ENVIRONMENTS. WHERE ST PRODUCTS ARE NOT DESIGNED FOR SUCH USE, THE PURCHASER SHALL USE PRODUCTS AT PURCHASER'S SOLE RISK, EVEN IF ST HAS BEEN INFORMED IN WRITING OF SUCH USAGE, UNLESS A PRODUCT IS EXPRESSLY DESIGNATED BY ST AS BEING INTENDED FOR "AUTOMOTIVE, AUTOMOTIVE SAFETY OR MEDICAL" INDUSTRY DOMAINS ACCORDING TO ST PRODUCT DESIGN SPECIFICATIONS. PRODUCTS FORMALLY ESCC, QML OR JAN QUALIFIED ARE DEEMED SUITABLE FOR USE IN AEROSPACE BY THE CORRESPONDING GOVERNMENTAL AGENCY.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2014 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

